

SPTECH Silicon NPN Power Transistor

BUX48A

DESCRIPTION

- High Voltage Capability
- High Current Capability
- Fast Switching Speed

APPLICATIONS

Designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switchmode applications such as:

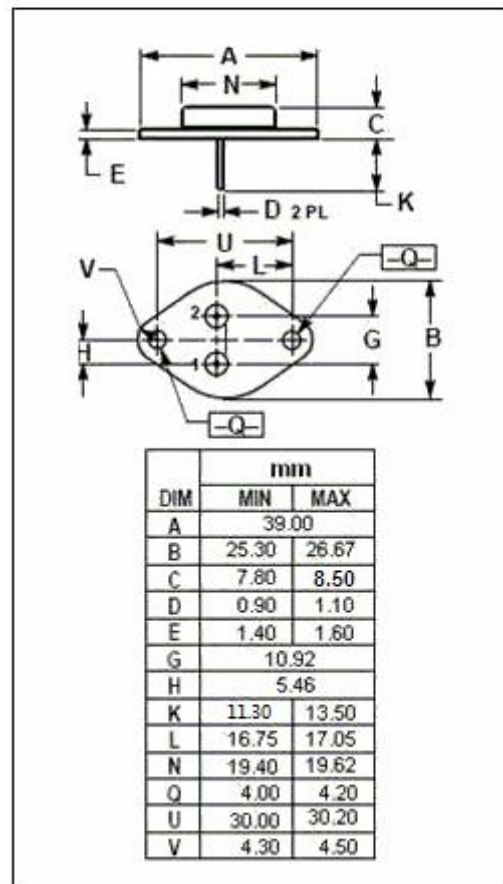
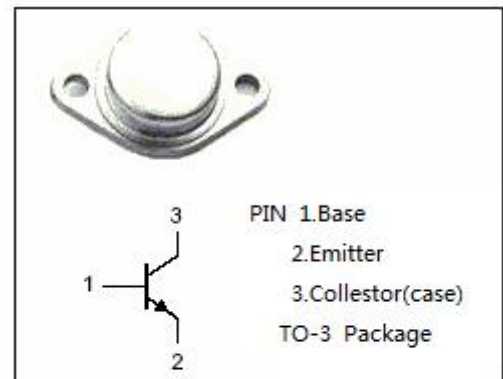
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEX}	Collector-Emitter Voltage ($V_{BE} = -1.5\text{V}$)	1000	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	4	A
I_{BM}	Base Current-peak	20	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	175	W
T_j	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



SPTECH Silicon NPN Power Transistor

BUX48A

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=20\text{mA}$; $I_B=0$	450		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\text{mA}$; $I_C=0$	7		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}$; $I_B=1.6\text{A}$ $I_C=8\text{A}$; $I_B=1.6\text{A}$; $T_C=100^{\circ}\text{C}$		1.5 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=12\text{A}$; $I_B=2.4\text{A}$		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8\text{A}$; $I_B=1.6\text{A}$ $I_C=8\text{A}$; $I_B=1.6\text{A}$; $T_C=100^{\circ}\text{C}$		1.6 1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CE}=1000\text{V}$; $I_E=0$ $V_{CE}=100\text{V}$; $I_E=0$; $T_C=125^{\circ}\text{C}$		0.2 2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}$; $I_C=0$		0.1	mA
h_{FE}	DC Current Gain	$I_C=8\text{A}$; $V_{CE}=5\text{V}$	8		
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$, $f_{\text{test}}=1\text{MHz}$		350	pF